

MOSFET – Power, N-Channel, SUPERFET® III, Easy-Drive 650 V, 24 A, 125 mΩ

FCMT125N65S3

General Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET Easy-drive series helps manage EMI issues and allows for easier design implementation.

The Power88 package is an ultra-slim surface-mount package (1 mm high) with a low profile and small footprint (8 × 8 mm²). SUPERFET III MOSFET in a Power88 package offers excellent switching performance due to lower parasitic source inductance and separated power and drive sources. Power88 offers Moisture Sensitivity Level 1 (MSL 1).

Features

- 700 V @ T_J = 150°C
- Typ R_{DS(on)} = 100 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 49 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 406 pF)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

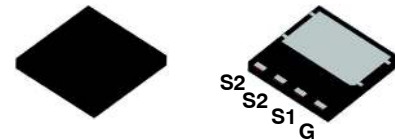
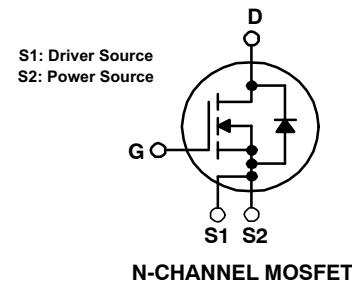
- Telecom / Server Power Supplies
- Industrial Power Supplies
- UPS / Solar



ON Semiconductor®

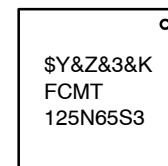
www.onsemi.com

| V _{DSS} | R _{DS(ON)} MAX | I _D MAX |
|------------------|-------------------------|--------------------|
| 650 V | 125 mΩ @ 10 V | 24 A |



PQFN4 8X8 2P
CASE 483AP

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Data Code (Year & Week)
&K = Lot
FCMT125N65S3 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FCMT125N65S3

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise noted)

| Symbol | Parameter | | Value | Unit |
|-----------------------------------|--|-------------------------------------|-------------|------|
| V _{DSS} | Drain to Source Voltage | | 650 | V |
| V _{GSS} | Gate to Source Voltage | DC | ±30 | V |
| | | AC (f > 1 Hz) | ±30 | V |
| I _D | Drain Current | Continuous (T _C = 25°C) | 24 | A |
| | | Continuous (T _C = 100°C) | 15 | |
| I _{DM} | Drain Current | Pulsed (Note 1) | 60 | A |
| E _{AS} | Single Pulsed Avalanche Energy (Note 2) | | 115 | mJ |
| I _{AS} | Avalanche Current (Note 2) | | 3.7 | A |
| E _{AR} | Repetitive Avalanche Energy (Note 1) | | 1.81 | mJ |
| dv/dt | MOSFET dv/dt | | 100 | V/ns |
| | Peak Diode Recovery dv/dt (Note 3) | | 20 | |
| P _D | Power Dissipation | (T _C = 25°C) | 181 | W |
| | | Derate Above 25°C | 1.45 | W/°C |
| T _J , T _{STG} | Operating and Storage Temperature Range | | -55 to +150 | °C |
| T _L | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 s | | 300 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 3.7 A, R_G = 25 Ω starting T_J = 25°C
3. I_{SD} ≤ 12 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C

THERMAL CHARACTERISTICS

| Symbol | Parameter | Value | Unit |
|------------------|--|-------|------|
| R _{θJC} | Thermal Resistance, Junction to Case, Max. | 0.69 | °C/W |
| R _{θJA} | Thermal Resistance, Junction to Ambient, Max. (Note 4) | 45 | |

4. Device on 1 in² pad 2 oz copper pad on 1.5 × 1.5 in. board of FR-4 material.

ORDERING INFORMATION

| Device | Marking | Package | Reel Size | Tape Width | Quantity [†] |
|--------------|--------------|---------|-----------|------------|-----------------------|
| FCMT125N65S3 | FCMT125N65S3 | PQFN8 | 13" | 13.3 mm | 3000 Units |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

FCMT125N65S3

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|-------------------------------------|---|--|-----|------|------|------|
| BV _{DSS} | Drain to Source Breakdown Voltage | V _{GS} = 0 V, I _D = 1 mA, T _J = 25°C | 650 | | | V |
| | | V _{GS} = 0 V, I _D = 1 mA, T _J = 150°C | 700 | | | V |
| ΔBV _{DSS} /ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = 1 mA, Referenced to 25°C | | 0.68 | | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 650 V, V _{GS} = 0 V | | | 10 | μA |
| | | V _{DS} = 520 V, T _C = 125°C | | 1.35 | | |
| I _{GSS} | Gate to Body Leakage Current | V _{GS} = ±30 V, V _{DS} = 0 V | | | ±100 | nA |

ON CHARACTERISTICS

| | | | | | | |
|---------------------|--------------------------------------|--|-----|-----|-----|----|
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} = V _{DS} , I _D = 0.59 mA | 2.5 | | 4.5 | V |
| R _{DS(on)} | Static Drain to Source On Resistance | V _{GS} = 10 V, I _D = 12 A | | 100 | 125 | mΩ |
| g _{FS} | Forward Transconductance | V _{DS} = 20 V, I _D = 12 A | | 16 | | S |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|------------------------|-----------------------------------|--|--|------|--|----|
| C _{iss} | Input Capacitance | V _{DS} = 400 V, V _{GS} = 0 V, f = 1 MHz | | 1920 | | pF |
| C _{oss} | Output Capacitance | | | 44 | | pF |
| C _{oss(eff.)} | Effective Output Capacitance | V _{DS} = 0 V to 400 V, V _{GS} = 0 V | | 406 | | pF |
| C _{oss(er.)} | Energy Related Output Capacitance | V _{DS} = 0 V to 400 V, V _{GS} = 0 V | | 63 | | pF |
| Q _{g(tot)} | Total Gate Charge at 10V | V _{DS} = 400 V, I _D = 12 A, V _{GS} = 10 V (Note 5) | | 49 | | nC |
| Q _{gs} | Gate to Source Gate Charge | | | 12 | | nC |
| Q _{gd} | Gate to Drain "Miller" Charge | | | 22 | | nC |
| ESR | Equivalent Series Resistance | f = 1 MHz | | 0.5 | | Ω |

SWITCHING CHARACTERISTICS

| | | | | | | |
|---------------------|---------------------|---|--|-----|--|----|
| t _{d(on)} | Turn-On Delay Time | V _{DD} = 400 V, I _D = 12 A, V _{GS} = 10 V, R _g = 4.7 Ω (Note 5) | | 22 | | ns |
| t _r | Turn-On Rise Time | | | 22 | | ns |
| t _{d(off)} | Turn-Off Delay Time | | | 60 | | ns |
| t _f | Turn-Off Fall Time | | | 5.8 | | ns |

SOURCE-DRAIN DIODE CHARACTERISTICS

| | | | | | | |
|-----------------|--|--|--|-----|-----|----|
| I _S | Maximum Continuous Source to Drain Diode Forward Current | | | 24 | | A |
| I _{SM} | Maximum Pulsed Source to Drain Diode Forward Current | | | 60 | | A |
| V _{SD} | Source to Drain Diode Forward Voltage | V _{GS} = 0 V, I _{SD} = 12 A | | | 1.2 | V |
| t _{rr} | Reverse Recovery Time | V _{DD} = 400 V, I _{SD} = 12 A, dI _F /dt = 100 A/μs | | 345 | | ns |
| Q _{rr} | Reverse Recovery Charge | | | 5.7 | | μC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

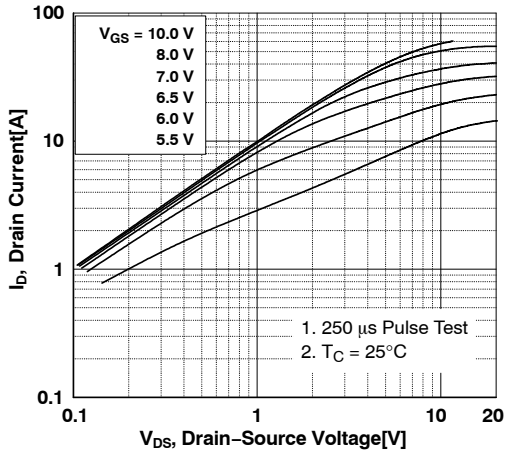


Figure 1. On-Region Characteristics

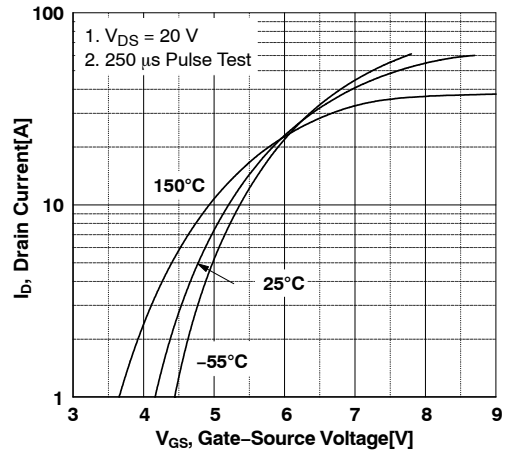


Figure 2. Transfer Characteristics

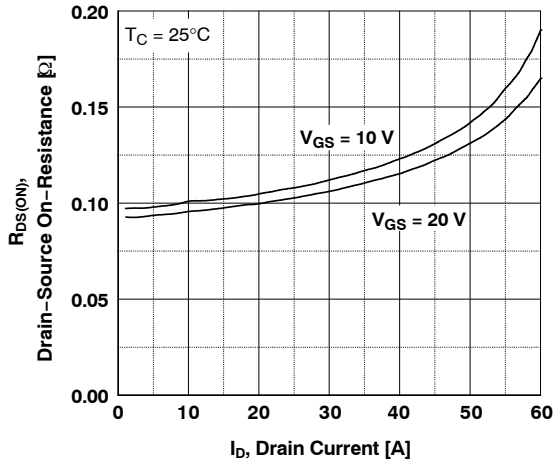


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

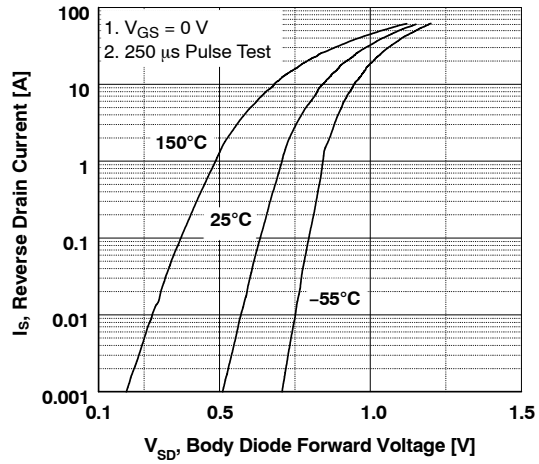


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

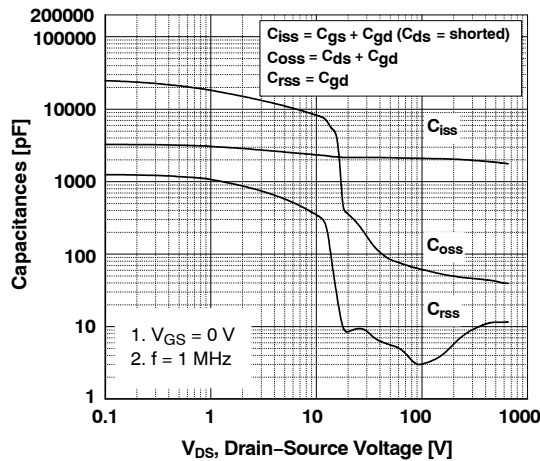


Figure 5. Capacitance Characteristics

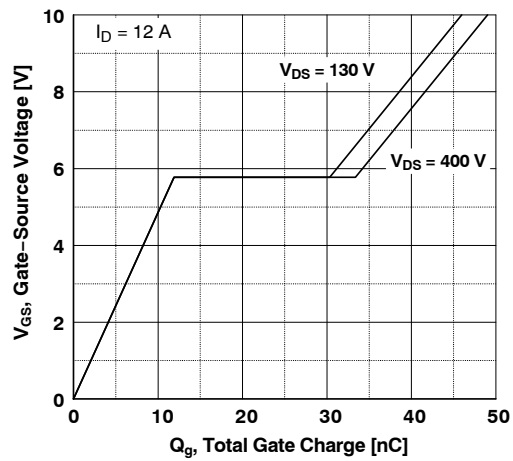


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

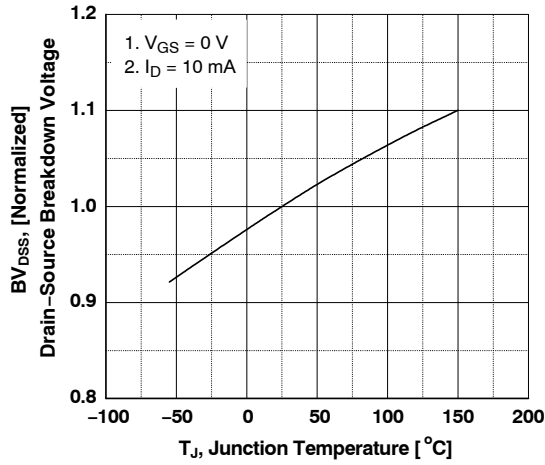


Figure 7. Breakdown Voltage Variation vs. Temperature

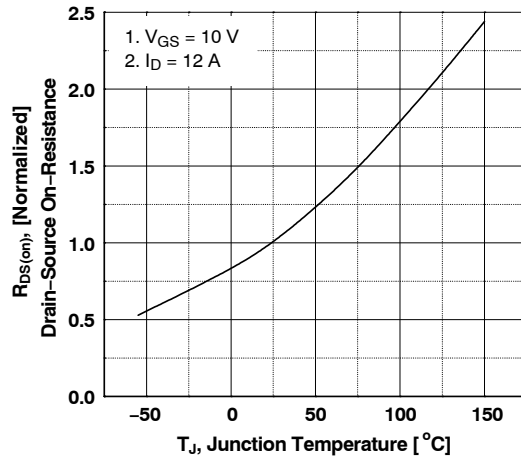


Figure 8. On-Resistance Variant vs. Temperature

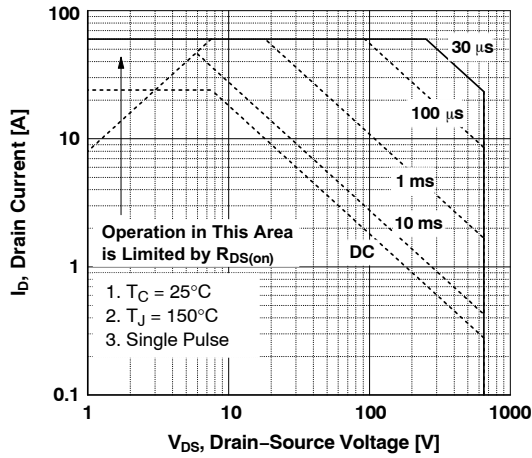


Figure 9. Maximum Safe Operation Area

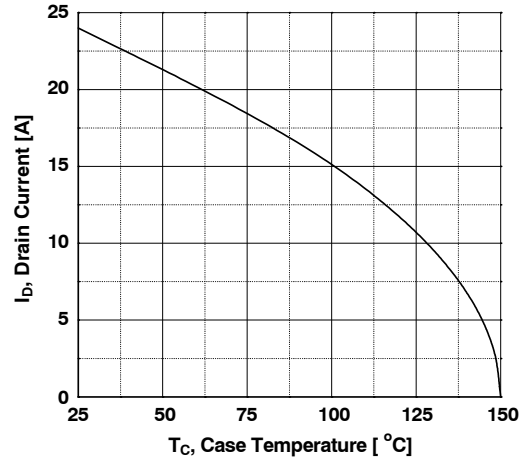


Figure 10. Maximum Drain Current vs. Case Temperature

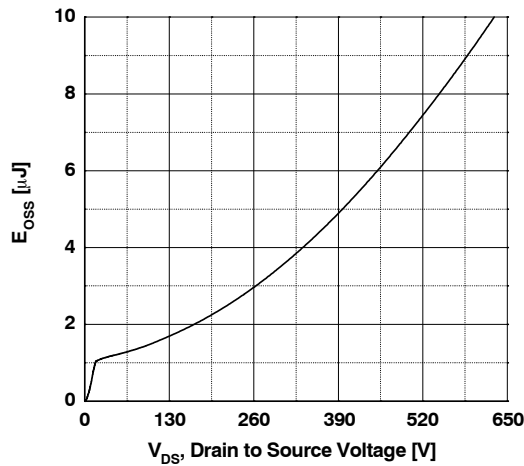


Figure 11. E_{OSS} vs. Drain to Source Voltage

FCMT125N65S3

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

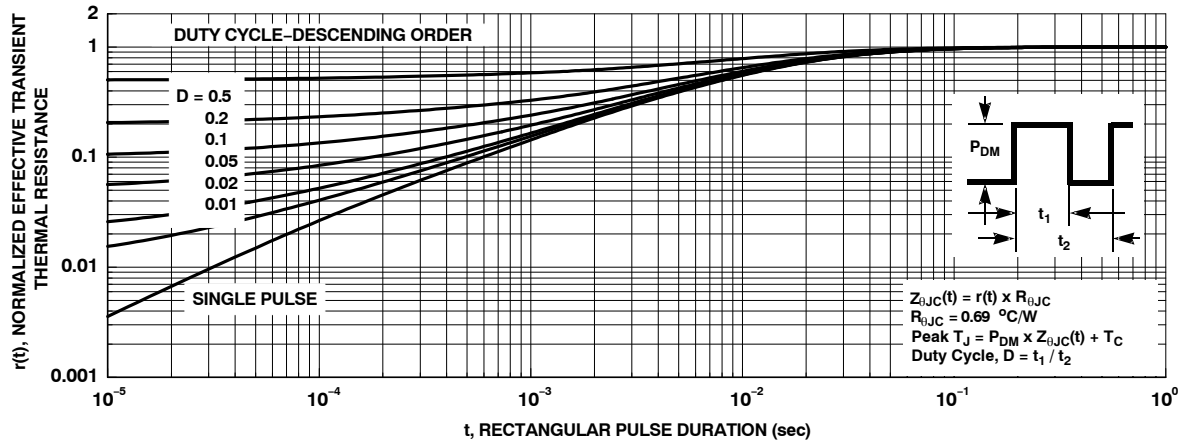


Figure 12. Transient Thermal Response Curve

FCMT125N65S3

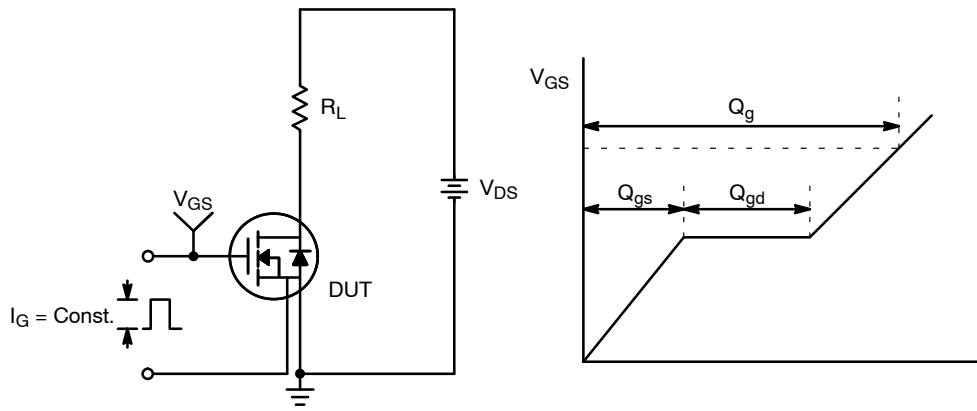


Figure 13. Gate Charge Test Circuit & Waveform

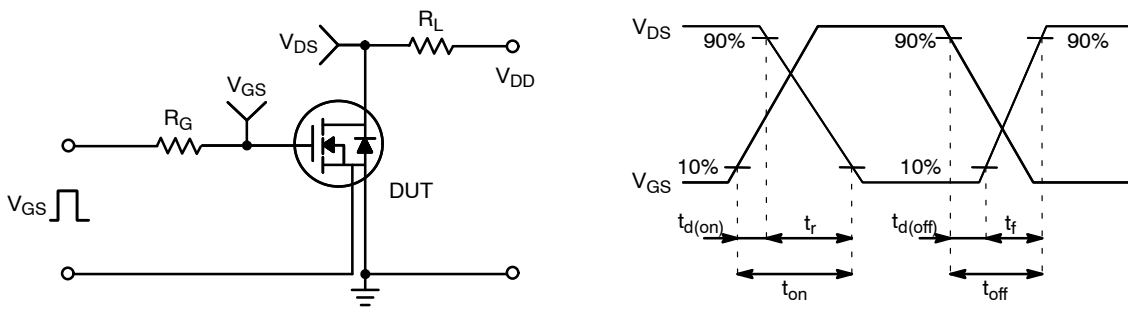


Figure 14. Resistive Switching Test Circuit & Waveforms

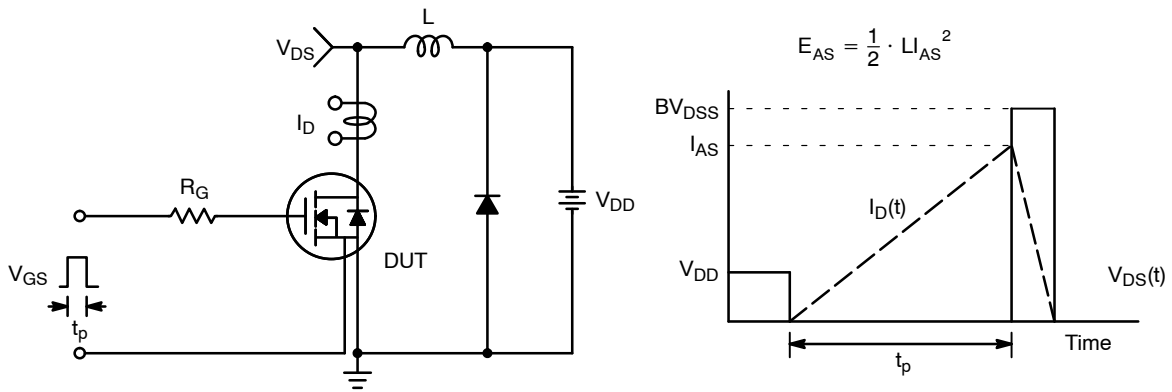


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

FCMT125N65S3

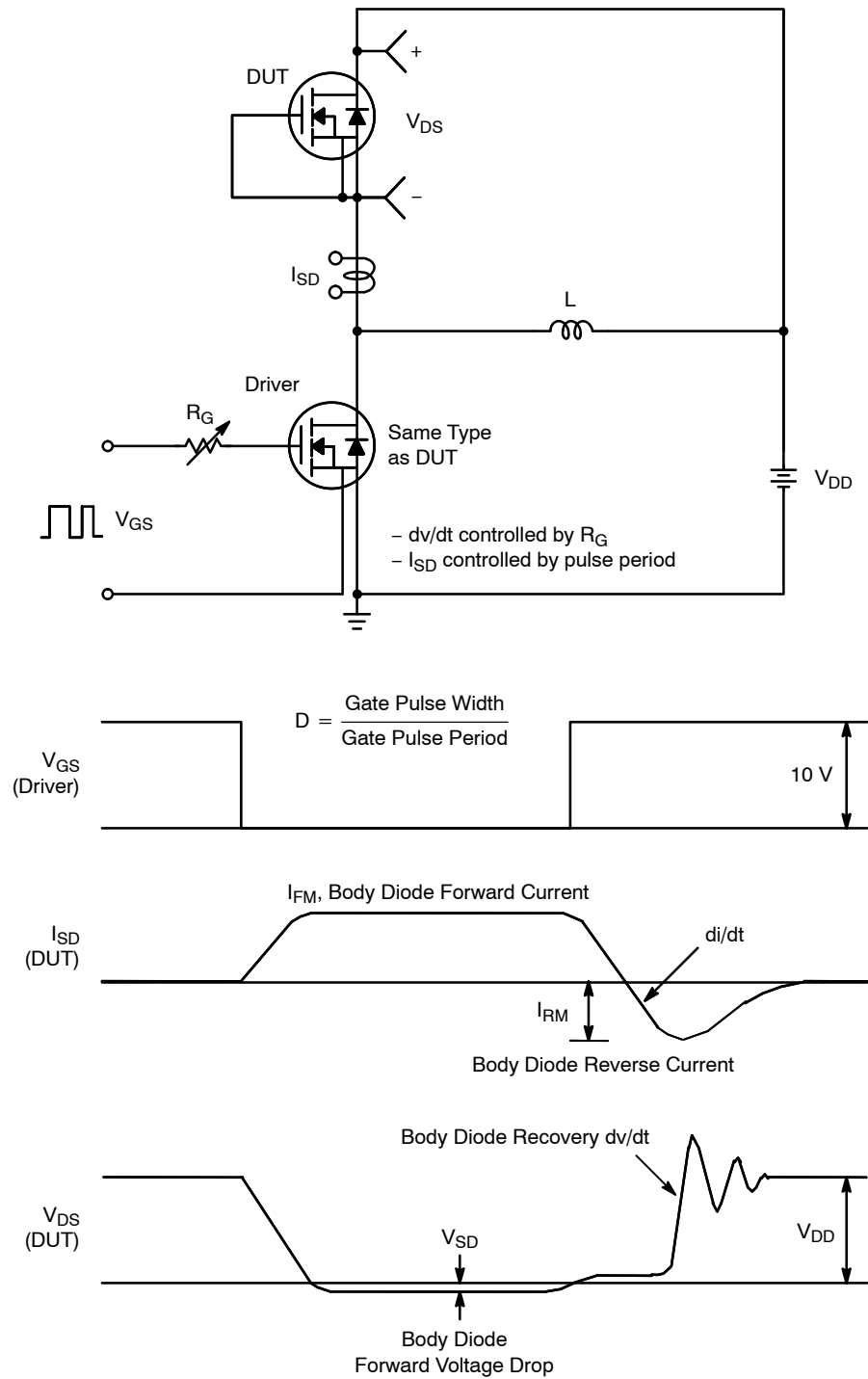


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

MECHANICAL CASE OUTLINE

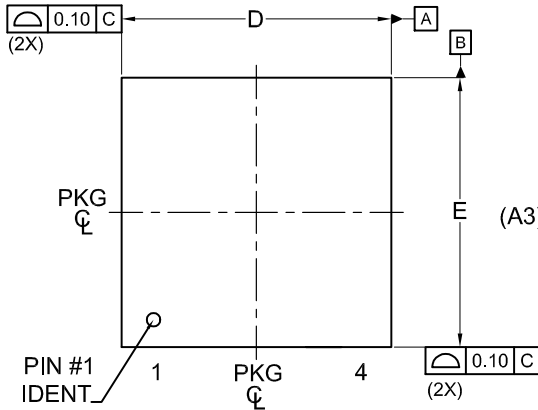
PACKAGE DIMENSIONS

ON Semiconductor®



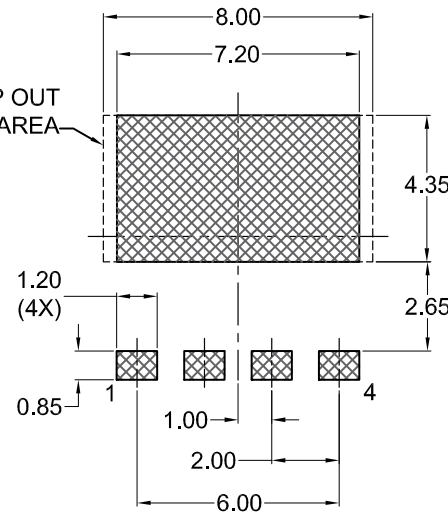
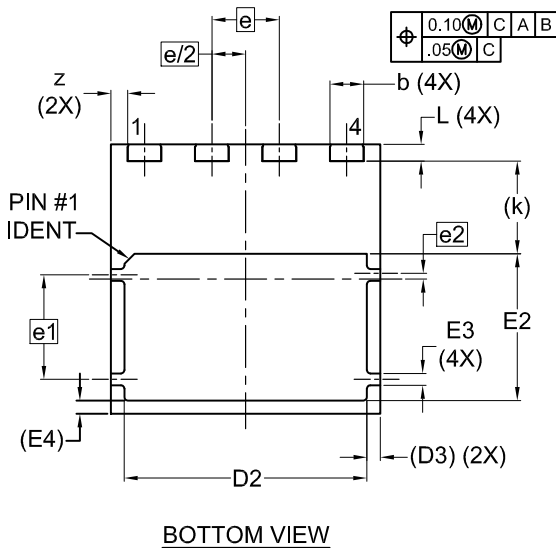
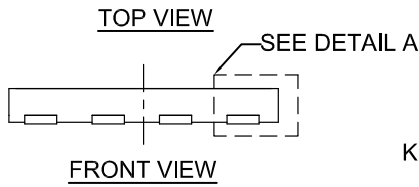
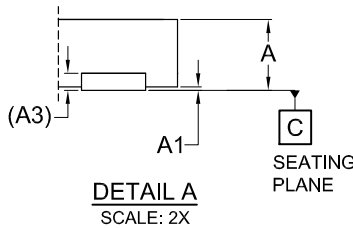
PQFN4 8X8, 2P
CASE 483AP
ISSUE A

DATE 06 JUL 2021



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
6. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.



| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | - | 0.05 |
| A3 | 0.20 REF | | |
| b | 0.90 | 1.00 | 1.10 |
| D | 7.90 | 8.00 | 8.10 |
| D2 | 7.10 | 7.20 | 7.30 |
| D3 | 0.40 REF | | |
| E | 7.90 | 8.00 | 8.10 |
| E2 | 4.25 | 4.35 | 4.45 |
| E3 | 0.25 | 0.35 | 0.45 |
| E4 | 0.40 REF | | |
| e | 2.00 BSC | | |
| e/2 | 1.00 BSC | | |
| e1 | 3.10 BSC | | |
| e2 | 0.17 BSC | | |
| k | 2.75 REF | | |
| L | 0.40 | 0.50 | 0.60 |

LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

| | | |
|-------------------------|----------------------|--|
| DOCUMENT NUMBER: | 98AON13664G | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| DESCRIPTION: | PQFN4 8X8, 2P | PAGE 1 OF 1 |

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales